L Number	Hits	Search Text	DB	Time stamp
1	2908855	memory or storage	USPAT;	2004/09/30 16:31
			US-PGPUB;	]
			EPO; JPO;	
			DERWENT	
2	152746	(memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/09/30 16:23
-	2227 13	floating adj gate or charge adj2 layer)	US-PGPUB;	2001/03/30 10:23
		l live and gate or area go days layery	EPO; JPO;	
1			DERWENT	
4	973	((memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/09/30 16:04
'	]	floating adj gate or charge adj2 layer)) and cell with bit with	US-PGPUB;	200 1/05/50 10.04
		(left or right)	EPO; JPO;	
		(left of right)	DERWENT	
5	10	(((memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/09/30 16:10
	10	floating adj gate or charge adj2 layer)) and cell with bit with	US-PGPUB;	2004/03/30 10:10
		(left or right)) and compar\$5 with (detect\$5 or check\$5)	EPO; JPO;	
	4556	with (first or left or right) with bit	DERWENT	2004/00/20 45 40
6	4556	(memory or storage) and two adj bit with cell	USPAT;	2004/09/30 16:12
			US-PGPUB;	
			EPO; JPO;	
1_			DERWENT	
7	2016	((memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/09/30 16:13
		floating adj gate or charge adj2 layer)) and ((memory or	US-PGPUB;	
		storage) and two adj bit with cell)	EPO; JPO;	
			DERWENT	
8	623	(((memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/09/30 16:33
		floating adj gate or charge adj2 layer)) and ((memory or	US-PGPUB;	
		storage) and two adj bit with cell)) and read\$5 with (voltage	EPO; JPO;	
		or potenital or level) with drain	DERWENT	
9	0	((((memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/09/30 16:15
		floating adj gate or charge adj2 layer)) and ((memory or	US-PGPUB;	
		storage) and two adj bit with cell)) and read\$5 with (voltage	EPO; JPO;	
		or potenital or level) with drain) and write adj verify with	DERWENT	
		(voltage or potenital or level) with drain	İ	
10	0	((((memory or storage) and (nonvolatile or non-volatile or	USPAT;	2004/09/30 16:15
		floating adj gate or charge adj2 layer)) and ((memory or	US-PGPUB;	
		storage) and two adj bit with cell)) and read\$5 with (voltage	EPO; JPO;	
		or potenital or level) with drain) and write-verify with	DERWENT	
		(voltage or potenital or level) with drain		
11	0		USPAT;	2004/09/30 16:33
·		write-verify with (voltage or potenital or level) with drain	US-PGPUB;	,,
			EPO; JPO;	
			DERWENT	
12	2	((memory or storage) and two adj bit with cell) and write	USPAT;	2004/09/30 16:16
		near2 verify with (voltage or potenital or level) with drain	US-PGPUB;	
		, \	EPO; JPO;	
			DERWENT	
13	86406	(memory or storage) and trap\$5	USPAT;	2004/09/30 16:24
•	00100	\	US-PGPUB;	200 1, 05, 50 10.24
			EPO; JPO;	
			DERWENT	
14	1339	((memory or storage) and trap\$5 ) and read\$4 with drain	USPAT;	2004/09/30 16:26
* 7	1339	with (voltage or potential or level)	US-PGPUB;	2007/03/30 10.20
		with (voltage of potential of level)		
			EPO; JPO;	
16	5	(((memony or ctorage) and trants ) and readth with during	DERWENT	2004/00/20 46:27
16	5	(((memory or storage) and trap\$5 ) and read\$4 with drain	USPAT;	2004/09/30 16:27
		with (voltage or potential or level)) and write adj verify with	US-PGPUB;	
		drain with (voltage or potenital or level)	EPO; JPO;	
17	204042	(manage on phase on ) and (but on 191) and 2 (191	DERWENT	2004/00/05 : 5 5 5
17	201013	(memory or storage) and (two or '2') near2 (bit or state or	USPAT;	2004/09/30 16:33
		threshold or level)	US-PGPUB;	
			EPO; JPO;	
<u> </u>		1.4.27.47 DM Door 1	DERWENT	

18	2464	((memory or storage) and (two or '2') near2 (bit or state or threshold or level)) and read\$5 with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO;	2004/09/30 16:33
19	1	(((memory or storage) and (two or '2') near2 (bit or state or threshold or level)) and read\$5 with (voltage or potenital or	DERWENT USPAT; US-PGPUB;	2004/09/30 16:35
20	0	level) with drain) and write-verify with (voltage or potenital or level) with drain (((memory or storage) and (two or '2') near2 (bit or state or	EPO; JPO; DERWENT USPAT;	2004/09/30 16:37
24		threshold or level)) and read\$5 with (voltage or potenital or level) with drain) and writing near2 verify with (voltage or potenital or level) with drain	US-PGPUB; EPO; JPO; DERWENT	2004/20/20 46 27
21	0	(((memory or storage) and (two or '2') near2 (bit or state or threshold or level)) and read\$5 with (voltage or potenital or level) with drain) and writing near2 verifying with (voltage or potenital or level) with drain	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/30 16:37